



DC COMPONENTS CO., LTD.
DISCRETE SEMICONDUCTORS

DXT2907A

TECHNICAL SPECIFICATIONS OF PNP EPITAXIAL PLANAR TRANSISTOR

Description

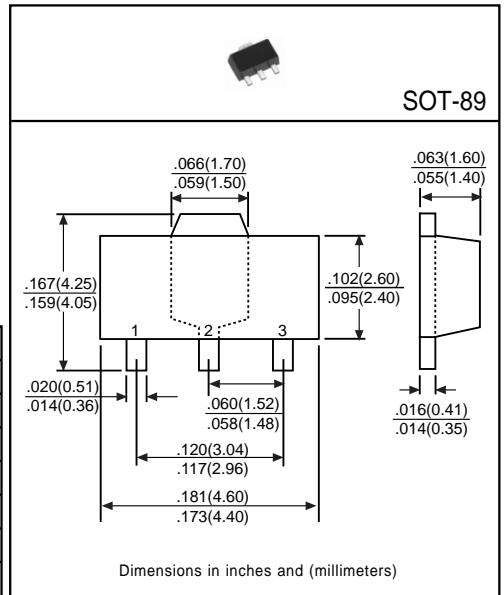
Designed for general purpose amplifier and high-speed, medium-power switching applications.

Pinning

- 1 = Base
- 2 = Collector
- 3 = Emitter

Absolute Maximum Ratings (T_A=25°C)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V _{CB0}	-60	V
Collector-Emitter Voltage	V _{CEO}	-60	V
Emitter-Base Voltage	V _{EBO}	-5	V
Collector Current	I _C	-600	mA
Total Power Dissipation	P _D	1.2	W
Junction Temperature	T _J	+150	°C
Storage Temperature	T _{STG}	-55 to +150	°C



Electrical Characteristics

(Ratings at 25°C ambient temperature unless otherwise specified)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Conditions
Collector-Base Breakdown Voltage	BV _{CB0}	-60	-	-	V	I _C =-10μA
Collector-Emitter Breakdown Voltage	BV _{CEO}	-60	-	-	V	I _C =-10mA
Emitter-Base Breakdown Voltage	BV _{EBO}	-5	-	-	V	I _E =-10μA
Collector Cutoff Current	I _{CBO}	-	-	-10	nA	V _{CB} =-50V
	I _{CEX}	-	-	-50	nA	V _{CE} =-30V, V _{BE} =-0.5V
Collector-Emitter Saturation Voltage ⁽¹⁾	V _{CE(sat)1}	-	-0.2	-0.4	mV	I _C =-150mA, I _B =-15mA
	V _{CE(sat)2}	-	-0.5	-1.6	V	I _C =-500mA, I _B =-50mA
Base-Emitter Saturation Voltage ⁽¹⁾	V _{BE(sat)1}	-	-	-1.3	V	I _C =-150mA, I _B =-15mA
	V _{BE(sat)2}	-	-	-2.6	V	I _C =-500mA, I _B =-50mA
DC Current Gain ⁽¹⁾	h _{FE1}	75	-	-	-	I _C =-100μA, V _{CE} =-10V
	h _{FE2}	100	-	-	-	I _C =-1mA, V _{CE} =-10V
	h _{FE3}	100	-	-	-	I _C =-10mA, V _{CE} =-10V
	h _{FE4}	100	-	300	-	I _C =-150mA, V _{CE} =-10V
	h _{FE5}	50	-	-	-	I _C =-500mA, V _{CE} =-10V
Transition Frequency	f _T	200	-	-	MHz	V _{CE} =-20V, f=100MHz, I _C =-50mA
Output Capacitance	C _{ob}	-	-	8	pF	V _{CB} =-10V, f=1MHz

(1)Pulse Test: Pulse Width ≤ 380μs, Duty Cycle ≤ 2%